



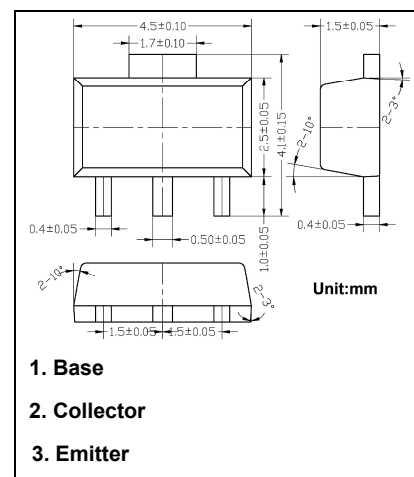
SOT-89 Plastic-Encapsulate Transistor

2SB772

Transistor (PNP)

Features

- Low speed switching

Marking: **B772**

Maximum Ratings ($T_a=25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-40	V
V_{CEO}	Collector-Emitter Voltage	-30	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current	-3	A
P_C	Collector Power Dissipation	0.5	W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	250	$^{\circ}\text{C/W}$
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature	-55~150	$^{\circ}\text{C}$

Electrical Characteristics ($T_a=25\text{ }^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C = -10\text{mA}$, $I_B = 0$	-30			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C = -100\mu\text{A}$, $I_E = 0$	-40			
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E = -100\mu\text{A}$, $I_C = 0$	-6			
I_{CBO}	Collector cutoff current	$V_{CB} = -40\text{V}$, $I_E = 0$			-1	μA
I_{CEO}	Collector cut-off current	$V_{CE} = -30\text{V}$, $I_B = 0$			-10	μA
I_{EBO}	Emitter cutoff current	$V_{EB} = -6\text{V}$, $I_C = 0$			-1	μA
$h_{FE(1)}$	DC current gain	$V_{CE} = -5\text{V}$, $I_C = -1\text{mA}$	60			
$h_{FE(2)}$		$V_{CE} = -5\text{V}$, $I_C = -10\text{mA}$	50			
$h_{FE(3)}$		$V_{CE} = -2\text{V}$, $I_C = -1\text{A}$	60		400	
V_{CEsat}	Collector-emitter saturation voltage	$I_C = -2\text{A}$, $I_B = -0.2\text{A}$			-0.45	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = -2\text{A}$, $I_B = -0.2\text{A}$			-1.50	
f_T	Current Gain Bandwidth Product	$I_C = -0.1\text{A}$, $V_{CE} = -5\text{V}$, $f=10\text{MHz}$	50			MHz

Classification Of $h_{FE(1)}$

Rank	R	O	Y	GR
Range	60-120	100-200	160-320	200-400

Typical Electrical Characteristics

